

33. (Twice Amended) A semiconductor device comprising:

a substrate having an insulating surface;

a first thin film transistor formed over said substrate, said first thin film transistor comprising:

a first semiconductor film comprising crystalline silicon formed over said substrate and having a channel region;

a first insulating film adjacent to said first semiconductor film; and

a first gate electrode adjacent to said first gate insulating film;

a second thin film transistor formed over said substrate, said second thin film transistor comprising:

a second semiconductor film comprising crystalline silicon formed over said substrate and having a channel region;

a second gate insulating film adjacent to said second semiconductor film; and

a second gate electrode adjacent to said second gate insulating film,

wherein said first semiconductor film contains germanium at a higher concentration than said second semiconductor film and the second semiconductor film is not intentionally added with germanium.

Please add the following new claims:

49 (New). A semiconductor device comprising:

a substrate;

a underlying layer formed over the substrate;

a first thin film transistor having a first active layer comprising $\text{Si}_{1-x}\text{Ge}_x$ where $0 < X < 1$ formed over said underlying layer; and